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|  | <h2>SI7478DP-T1-GE3</h2> |
| | <p>Hersteller-Teilenummer: SI7478DP-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 60V 15A PPAK SO-8</p> <p>Datenblätter:  SI7478DP-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 19838 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |
| <p>Image may be representation. See specs for product details.</p> | |

Spezifikationen

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| Teilenummer | SI7478DP-T1-GE3 |
| Hersteller | Electro-Films (EFI) / Vishay |
| Beschreibung | MOSFET N-CH 60V 15A PPAK SO-8 |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs, |
| Teilstatus | 19838 pcs Stock |
| Hersteller Standard Vorlaufzeit | 33 Weeks |
| detaillierte Beschreibung | N-Channel 60V 15A (Ta) 1.9W (Ta) Surface Mount |
| Serie | TrenchFET® |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | PowerPAK® SO-8 |
| Supplier Device-Gehäuse | PowerPAK® SO-8 |
| Verlustleistung (max) | 1.9W (Ta) |
| Typ FET | N-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 60V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 15A (Ta) |
| Rds On (Max) @ Id, Vgs | 7.5 mOhm @ 20A, 10V |
| VGS (th) (Max) @ Id | 3V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 160nC @ 10V |
| Antriebsspannung (Max Rds On, Min Rds On) | 4.5V, 10V |
| Vgs (Max) | ±20V |
| Verpackung | Tape & Reel (TR) |
| Bleifreier Status / RoHS-Status | Lead free / RoHS Compliant |
| Feuchtigkeitsempfindlichkeitsniveau (MSL) | 1 (Unlimited) |
| Andere Namen | SI7478DP-T1-GE3TR |

SI7478DP-T1-GE3 ist neu im Original, Suche SI7478DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7478DP-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7478DP-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

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|  <p>SI7478DP-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 60V 15A PPAK SO-8</p> |  <p>SI7478DP SI SI7478DP SI</p> |  <p>SI7478DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 60V 15A PPAK SO-8</p> |  <p>SI7483ADP-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 14A PPAK SO-8</p> |
|  <p>SI7483ADP-T1-E3 Vishay / Siliconix MOSFET P-CH 30V 14A PPAK SO-8</p> |  <p>SI7483ADP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 14A PPAK SO-8</p> |  <p>SI7476DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 40V 15A PPAK SO-8</p> |  <p>SI7478DP-T1-E3 Vishay / Siliconix MOSFET N-CH 60V 15A PPAK SO-8</p> |

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| SI7461DP-T1-E3 | SI7461DP-T1-GE3 | SI7461DP-T1-GE3 | SI7462DP-T1-E3 | SI7462DP-T1-E3 |
| SI7462DP-T1-GE3 | SI7462DP-T1-GE3 | SI7463ADP-T1-GE3 | SI7463ADP-T1-GE3 | SI7463DP-T1-GE3 |
| SI7463DP-T1-GE3 | SI7464DP-T1-E3 | SI7464DP-T1-E3 | SI7464DP-T1-GE3 | SI7464DP-T1-GE3 |
| SI7465DP-T1-E3 | SI7465DP-T1-E3 | SI7465DP-T1-GE3 | SI7465DP-T1-GE3 | SI7470DP-T1-GE3 |
| SI7476DP-T1-GE3 | SI7476DP-T1-GE3 | SI7478DP | SI7478DP-T1-E3 | SI7478DP-T1-E3 |
| SI7478DP-T1-GE3 | SI7483ADP | SI7483ADP-T1-E3 | SI7483ADP-T1-E3 | SI7483ADP-T1-GE3 |
| SI7483ADP-T1-GE3 | SI7483DP-T1 | SI7483DP-T1-E3 | SI7483DP-T1-GE3 | SI7485DP-T1-E3 |
| SI7485DP-T1-E3 | SI7485DP-T1-GE3 | SI7485DP-T1-GE3 | SI7489DP | SI7489DP-T1-GE3 |
| SI7489DP-T1-GE3 | SI7491DP | SI7491DP-T1-GE3 | SI7491DP-T1-GE3 | SI7501DN-T1-E3 |
| SI7501DN-T1-E3 | SI7540ADP-T1-GE3 | SI7540ADP-T1-GE3 | SI7540DP-T1-E3 | SI7540DP-T1-E3 |

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